

ABSTRACT OF THE DISCLOSURE

There is disclosed a method of producing a photovoltaic device, characterized in that it includes steps of: a step of forming a zinc oxide layer on a substrate at least by electrolytic deposition; subjecting the zinc oxide layer to any one treatment selected from the group consisting of plasma treatment with a rare gas or nitrogen gas, ion irradiation, light irradiation and electromagnetic irradiation; and forming on the zinc oxide layer a semiconductor layer that are made up of a non-single crystal silicon material containing hydrogen and have at least one p-i-n junction.